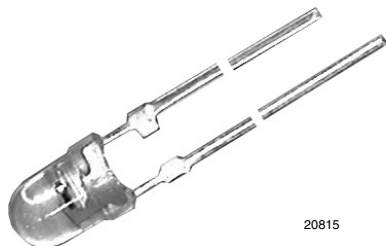


Ambient Light Sensor, RoHS Compliant



20815

FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm): $\varnothing 3$
- High photo sensitivity
- Adapted to human eye responsiveness
- Angle of half sensitivity: $\varphi = \pm 30^\circ$
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC


RoHS
COMPLIANT

DESCRIPTION

TEPT4400 ambient light sensor is a silicon NPN epitaxial planar phototransistor in a T-1 package. It is sensitive to visible light much like the human eye and has peak sensitivity at 570 nm.

APPLICATIONS

- Ambient light sensor for control of display backlight dimming in LCD displays and keypad backlighting of mobile devices and in industrial on/off-lighting operation
- Replacement of CdS photoresistors

PRODUCT SUMMARY

| COMPONENT | I_{PCE} (μA) | φ (deg) | $\lambda_{0.5}$ (nm) |
|-----------|-----------------------|-----------------|----------------------|
| TEPT4400 | 200 | ± 30 | 440 to 800 |

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM |
|---------------|-----------|---|--------------|
| TEPT4400 | Bulk | MOQ: 5000 pcs, 5000 pcs/bulk. Label with I_{PCE} group on each bulk. Specifications of group A/B/C see table "Type Dedicated Characteristics" | T-1 |

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
|-------------------------------------|----------------------------|------------|---------------|------------|
| Collector emitter voltage | | V_{CEO} | 6 | V |
| Emitter collector voltage | | V_{ECO} | 1.5 | V |
| Collector current | | I_C | 20 | mA |
| Power dissipation | $T_{amb} \leq 55^\circ C$ | P_V | 100 | mW |
| Junction temperature | | T_j | 100 | $^\circ C$ |
| Operating temperature range | | T_{amb} | - 40 to + 85 | $^\circ C$ |
| Storage temperature range | | T_{stg} | - 40 to + 100 | $^\circ C$ |
| Soldering temperature | $t \leq 3$ s | T_{sd} | 260 | $^\circ C$ |
| Thermal resistance junction/ambient | J-STD-051, soldered on PCB | R_{thJA} | 300 | K/W |

Note

$T_{amb} = 25^\circ C$, unless otherwise specified

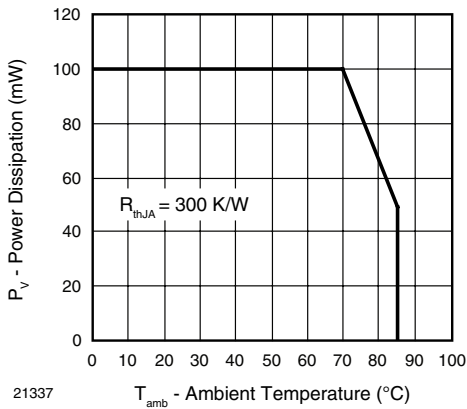


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS

| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
|--------------------------------------|---|-----------------|------|------------|------|---------------|
| Collector emitter breakdown voltage | $I_C = 0.1 \text{ mA}$ | V_{CEO} | 6 | | | V |
| Collector dark current | $V_{CE} = 5 \text{ V}, E = 0$ | I_{CEO} | | 3 | 50 | nA |
| Collector emitter capacitance | $V_{CE} = 0 \text{ V}, f = 1 \text{ MHz}, E = 0$ | C_{CEO} | | 16 | | pF |
| Collector light current | $E_V = 20 \text{ lx}, \text{CIE illuminant A}, V_{CE} = 5 \text{ V}$ | I_{PCE} | 15 | | 70 | μA |
| | $E_V = 100 \text{ lx}, \text{CIE illuminant A}, V_{CE} = 5 \text{ V}$ | I_{PCE} | | 200 | | μA |
| Angle of half sensitivity | | ϕ | | ± 30 | | deg |
| Wavelength of peak sensitivity | | λ_p | | 570 | | nm |
| Range of spectral bandwidth | | $\lambda_{0.5}$ | | 440 to 800 | | nm |
| Collector emitter saturation voltage | $E_V = 20 \text{ lx}, \text{CIE illuminant A}, I_{PCE} = 1.2 \mu\text{A}$ | V_{CEsat} | | 0.1 | | V |

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

TYPE DEDICATED CHARACTERISTICS

| PARAMETER | TEST CONDITION | SELECTION TYPE | SYMBOL | MIN. | MAX. | UNIT |
|---------------|--|----------------|-----------|------|------|---------------|
| Photo current | $E_V = 20 \text{ lx}, \text{CIE illuminant A}, V_{CE} = 5 \text{ V}$ | TEPT4400A | I_{PCE} | 15 | 28.4 | μA |
| | | TEPT4400B | I_{PCE} | 23.5 | 44.6 | μA |
| | | TEPT4400C | I_{PCE} | 36.9 | 70 | μA |

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

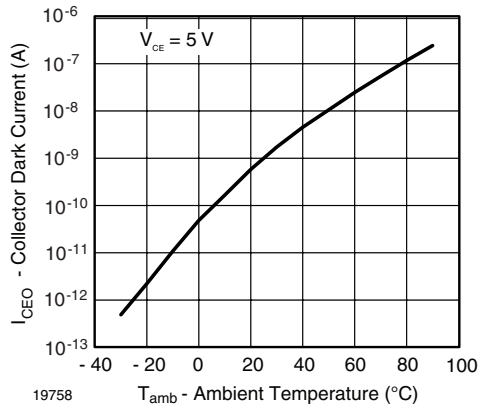


Fig. 2 - Collector Dark Current vs. Ambient Temperature

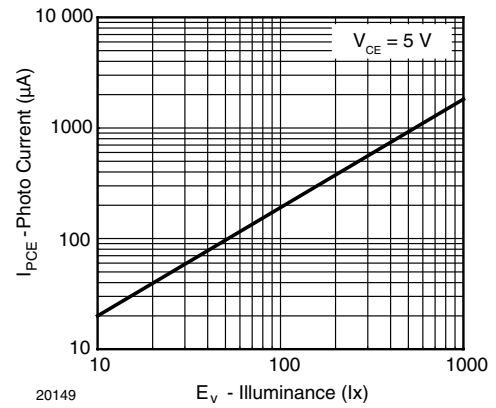


Fig. 5 - Photo Current vs. Illuminance

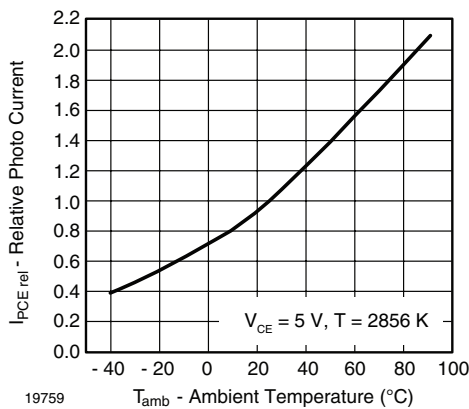


Fig. 3 - Relative Photo Current vs. Ambient Temperature

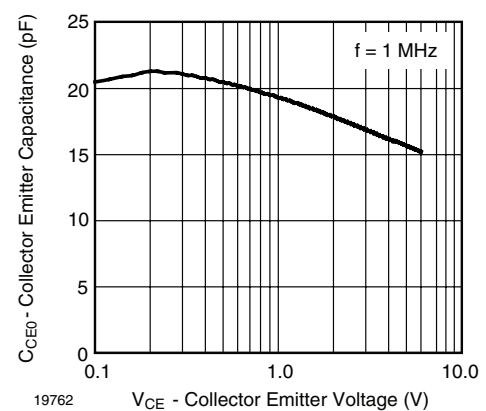


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

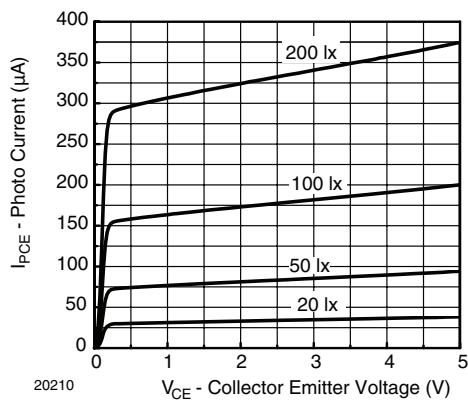


Fig. 4 - Photo Current vs. Collector Emitter Voltage

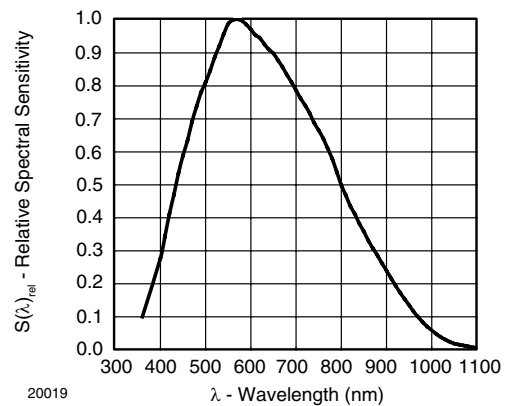


Fig. 7 - Relative Spectral Sensitivity vs. Wavelength

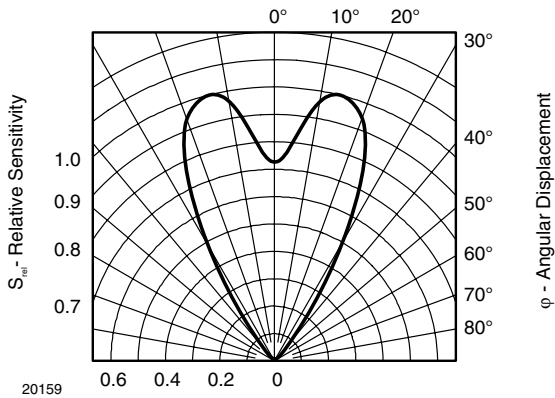
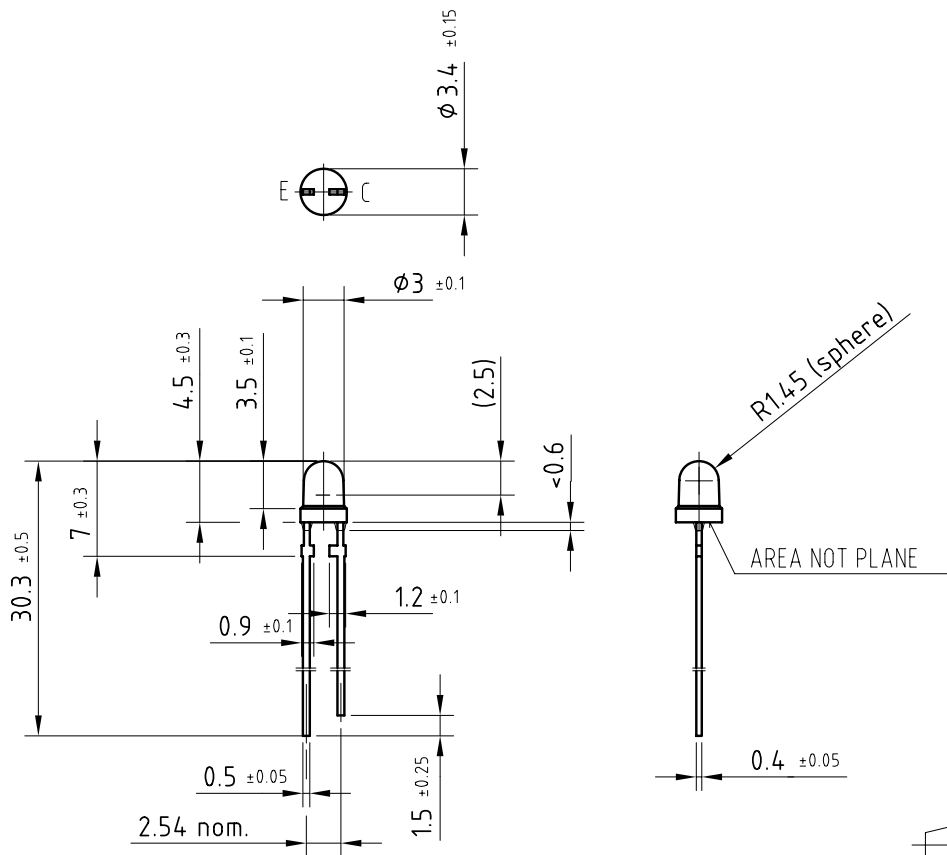


Fig. 8 - Relative Radiant Sensitivity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



technical drawings
according to DIN
specifications

Drawing-No.: 6.544-5054.01-4

Issue: 2; 12.11.96

96 12190



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